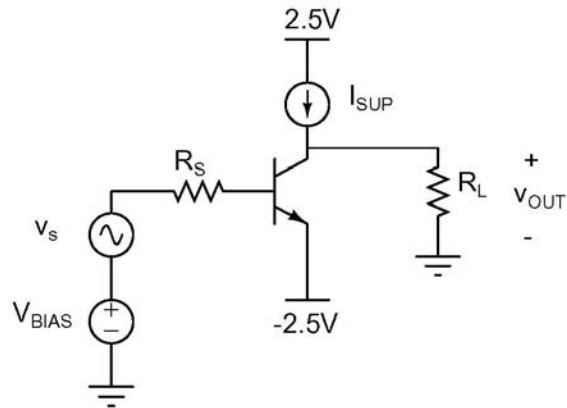


MASSACHUSETTS INSTITUTE OF TECHNOLOGY
Department of Electrical Engineering and Computer Science
6.012 Microelectronic Devices and Circuits
Homework #8

Problem 1: Howe and Sodini P10.6

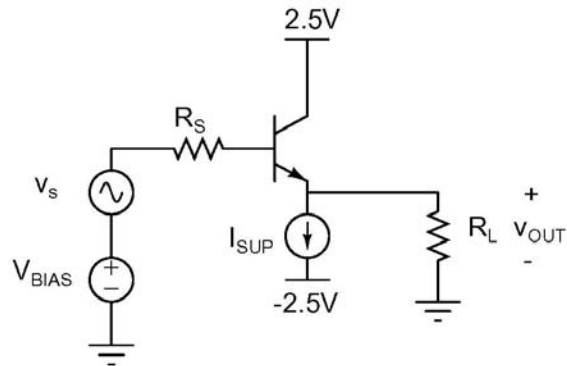
Problem 2:



| Device Parameters | |
|--------------------------|---|
| $I_{SUP}=250\mu\text{A}$ | $I_S=10^{-15}\text{A}$ |
| $R_S=5\text{k}\Omega$ | $\beta_F=\beta_o=100$ |
| $R_L=10\text{k}\Omega$ | $V_A=25\text{V}$ |
| $r_{oc}=\infty$ | $f_T=1\text{GHz @ } I_C=250\mu\text{A}$ |
| | $C_\mu=0.1\text{pF}$ |

- Calculate V_{BIAS} such that $V_{OUT}=0\text{V}$.
- Calculate the low frequency loaded voltage gain v_{out}/v_s .
- Calculate C_π from the device data.
- Use the Miller approximation to calculate ω_{3db} .
- Use the open-circuit time constant method to calculate ω_{3db} .

Problem 3:

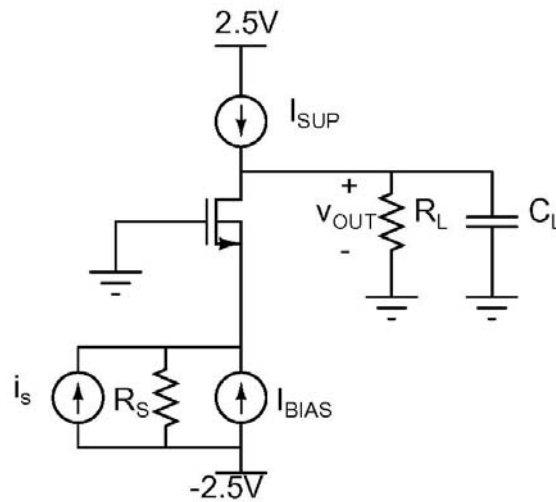


| Device Parameters | |
|-----------------------|-------------------|
| $R_L=10k\Omega$ | $C_{je0}=100fF$ |
| $R_S=5k\Omega$ | $\tau_F=100ps$ |
| $I_S=10^{-15}A$ | $C_{\mu0}=200fF$ |
| $\beta_F=\beta_o=100$ | $r_{oc}=\infty$ |
| $V_A=25V$ | $\Phi_{Bc}=0.75V$ |

In Problem 2, the high source resistance lowered ω_{3db} . One method of improving the frequency response is to precede the common emitter stage with a common-collector, CC, also called an emitter-follower stage. Under this condition the source resistance of the CE amplifier is the output resistance of the CC amplifier.

- Find I_{SUP} for the emitter follower such that its R_{out} equals 100Ω .
- Calculate V_{BIAS} such that $V_{OUT}=0V$.
- Calculate C_{π} and C_{μ} from the device data for the emitter-follower.
- Use the open-circuit time constant method to calculate ω_{3db} for the emitter-follower.

Problem 4:



| Device Parameters | |
|------------------------|----------------------------|
| $R_S=100k\Omega$ | $\mu_n C_{ox}=50\mu A/V^2$ |
| $R_L=1k\Omega$ | $C_{ox}=2.3fF/\mu m^2$ |
| $r_{oc}=\infty$ | $C_{Jn}=0.1fF/\mu m^2$ |
| $V_{Tn}=1V$ | $C_{JSWn}=0.5fF/\mu m$ |
| $\lambda_n=0.05V^{-1}$ | $L_{diffn}=6\mu m$ |
| | $C_{ov}=0.5fF/\mu m$ |

The frequency response of the NMOS common-gate amplifier depends on g_m , C_{gs} , C_{gd} , and C_L . One method of increasing g_m is to increase the bias current. Another method of increasing g_m is to increase the W of the device. However, as the width of the device is increased, the parasitic capacitances also increase. For this problem, let $C_L=C_{db}$. Assume that the amplifier is biased such that $V_{OUT}=0V$.

- Use the open-circuit time constant method to derive an expression for ω_{3db} for the common-gate amplifier including C_L .
- Use Matlab or Excel to plot ω_{3db} vs. I_{SUP} for $50\mu A < I_{SUP} < 500\mu A$. Use $W/L=50\mu m/2\mu m$.
- Use Matlab or Excel to plot ω_{3db} vs. W for $50\mu m < W < 500\mu m$. Use $I_{SUP}=100\mu A$.
- What is the effect of increasing I_{SUP} (for a constant W) on the frequency response of this amplifier? What are some potential drawbacks of this approach?
- What is the effect of increasing W (for a constant I_{SUP}) on the frequency response of this amplifier? What are some potential drawbacks of this approach?

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